

Silicon PNP Power Transistors

MJE371

DESCRIPTION

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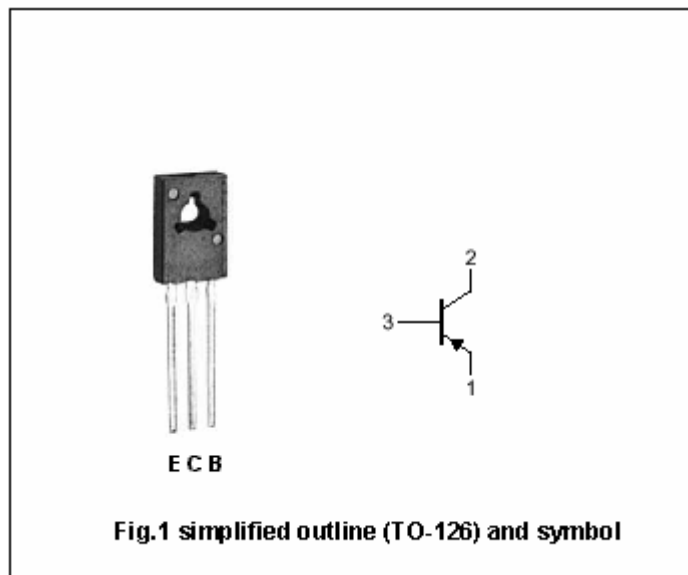
- With TO-126 package
- Complement to type MJE521

APPLICATIONS

- For use in general-purpose amplifier and switching circuits,
- Recommended for use in 5 to 20 W audio amplifiers utilizing complementary symmetry circuitry

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

ABSOLUTE MAXIMUM RATINGS($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current (DC)		-4	A
I_{CM}	Collector current-Peak		-8	A
I_B	Base current (DC)		-2	A
P_D	Total power dissipation	$T_c=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	3.12	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =-100mA ; I _B =0	-40			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-2.0A; I _B =-0.2A			-0.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-1V			-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-1V	40			

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PACKAGE OUTLINE

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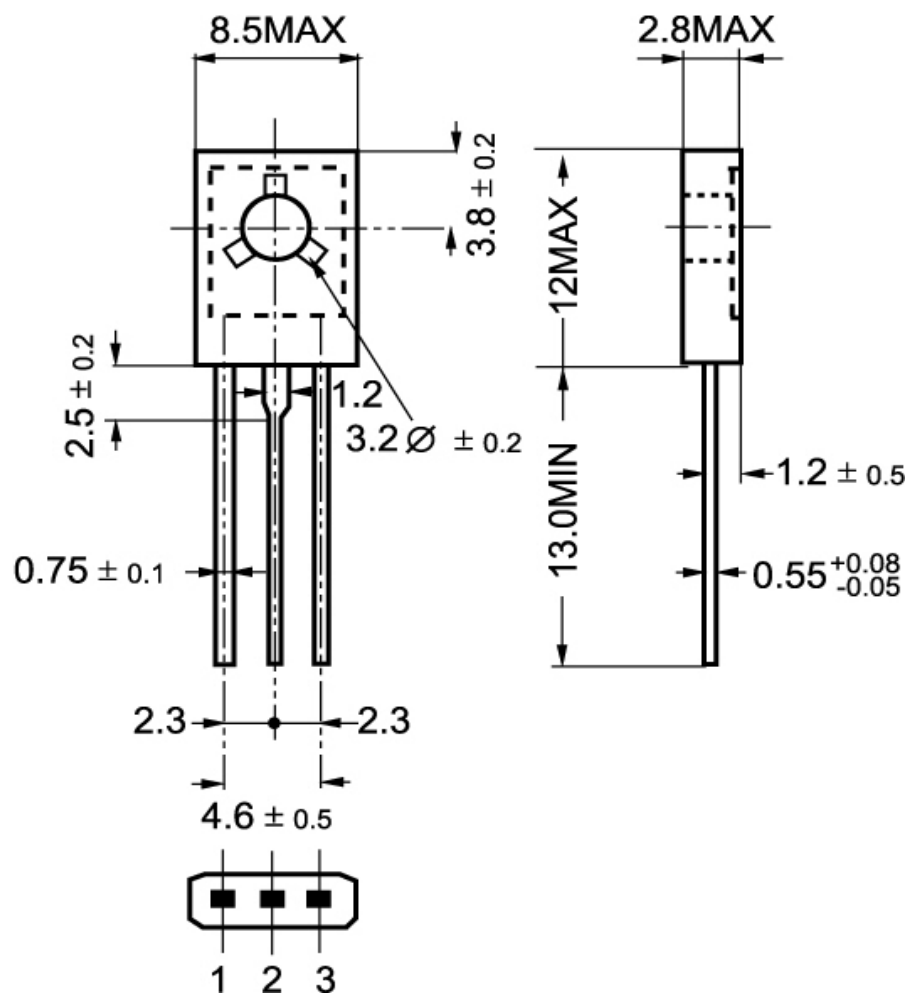


Fig.2 Outline dimensions